

IN THE SPECIFICATION

Please amend the Title on page 1 as follows:

NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE IN WHICH
SELECTION GATE TRANSISTORS AND MEMORY CELLS HAVE DIFFERENT
STRUCTURES AND METHOD OF MANUFACTURING THE SAME

Please replace the paragraph at page 71, lines 13-18, as follows:

Next, a resist mask is prepared, and an area in the channel region corresponding to the selection gate transistor is doped with a p-type impurity by ion implantation, whereby a region ~~[[14]]~~ 54 having a higher impurity concentration than that of the memory cell is formed (see FIG. 46). Then, gate electrodes are formed as in the fifth embodiment (see FIG. 46).